

2N1595-2N1599

SILICON THYRISTORS

High-reliability discrete products and engineering services since 1977

FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

Symbol	Ratings	2N1595	2N1596	2N1597	2N1598	2N1599	Unit
V _{RSM(REP)}	Peak reverse blocking voltage*	50	100	200	300	400	V
I _{T(RMS)}	Forward current RMS (all conduction angles)	1.6					
I _{TSM}	Peak surge current (one-cycle, 60Hz, T _J = -65 to +125°C)	15					
P_{GM}	Peak gate power – forward	0.1					
P _{G(AV)}	Average gate power – forward	0.01					
I _{GM}	Peak gate current – forward	0.1					
V_{GFM}	Peak gate voltage – forward	10					
V_{GRM}	Peak gate voltage – reverse	10					V
TJ	Operating junction temperature range	-65 to +125					°C
T _{STG}	Storage temperature range	-65 to +150					°C

MAXIMUM RATINGS

*V_{DRM} or V_{RSM} can be applied for all types on a continuous dc basis without incurring damage.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

Symbol	Ratings		2N1595	2N1596	2N1597	2N1598	2N1599	Unit	
V _{DRM}	Peak forward blocking voltage*	Min.	50	100	200	300	400	V	
I _{rrm}	Peak reverse blocking current (Rated V _{DRM} , T _J = 125°C)	Max.	1.0			mA			
I _{DRM}	Peak forward blocking current (Rated V_{DRM} with gate open, T_J = 125°C)	Max.	1.0			mA			
	Gate trigger current	Тур.	2.0				mA		
I _{GT}	Anode voltage = 7.0 Vdc, $R_L = 12\Omega$	Max.			10				
	Gate trigger voltage	Тур.		0.7					
V _{GT}	Anode voltage = 7.0Vdc, $R_L = 12\Omega$	Max.	Max. 3.0				v		
	V_{DRM} = rated, R_L = 100 Ω , T_J = 125°C	Min.			0.2				
I _H	Holding current Anode voltage = 7.0 Vdc, gate open	Тур.	5.0			mA			
N/	Forward on-voltage	Тур.			1.1			V	
V _{TM}	I _T = 1Adc	Max.			2.0			V	
t _{gt}	Turn-on time (t_d+t_r) I _{GT} = 10mA, I _T = 1A	Тур.	0.8		μs				
tq	Turn-off time $I_T = 1A$, $I_R = 1A$, $dv/dt = 20 V/\mu s$, $T_J = 125^{\circ}C$ $V_{DRM} = rated voltage$	Тур.			10			μs	

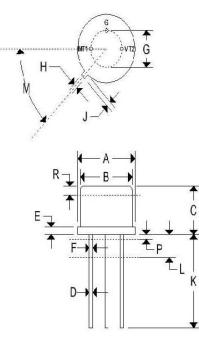
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MECHANICAL CHARACTERISTICS

Case:	ТО-39
Marking:	Body painted, alpha-numeric
Pin out:	See below



	TO-39					
	Inc	hes	Millimeters			
	Min	Max	Min	Max		
A	0.335	0.370	8.510	9.390		
В	0.305	0.335	7.750	8.500		
С	0.240	0.260	6.100	6.600		
D	0.016	0.021	0.410	0.530		
E	0.009	0.041	0.230	1.040		
F	0.016	0.019	0.410	0.480		
G	0.200 BSC		5.080 BSC			
Η	0.028	0.034	0.720	0.860		
J	0.029	0.045	0.740	1.140		
K	0.500	0.750	12.700	19.050		
L	0.250	171	6.350	151		
М	45°C BSC		45°C BSC			
Р		0.050	8 7 8	1.270		
R	0.100		2.540	121		

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